Low Vcesat NPN Epitaxial Planar Transistor

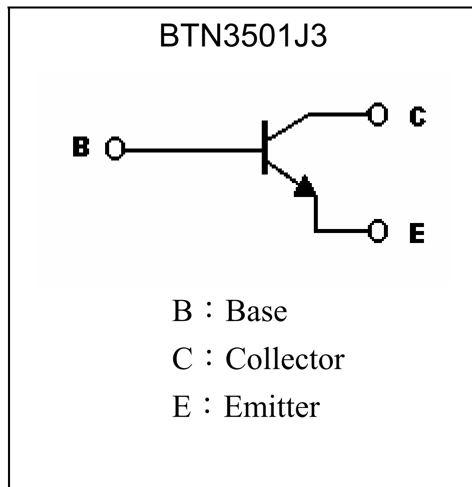
BTN3501J3

BV_{CEO}	80V
I_C	8A
V_{CESAT}	0.6V (max.)

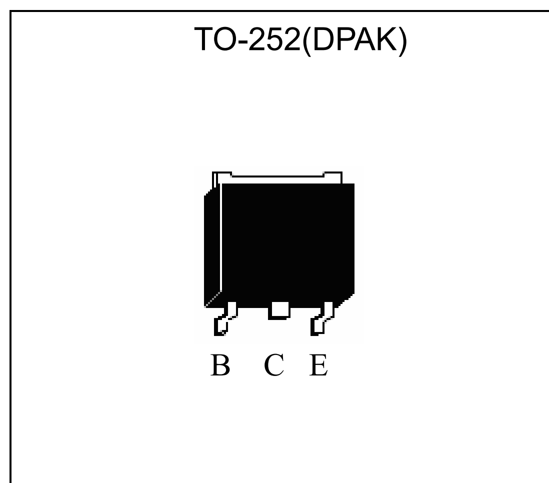
Features

- Low $V_{CE(sat)}$
- High BV_{CEO}
- Excellent current gain characteristics
- RoHS compliant package

Symbol

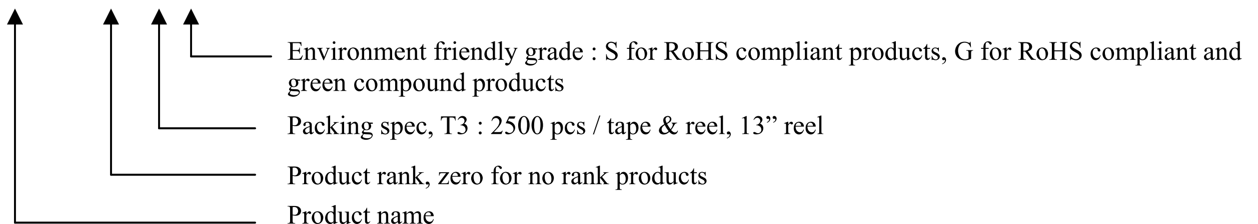


Outline



Ordering Information

Device	Package	Shipping
BTN3501J3-XX-T3-S	TO-252 (RoHS compliant package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	8	A
Collector Current (Pulse)	I_{CP}	16 (Note 1)	
Power Dissipation @ T_A=25℃	P_D	1.75 (Note 2)	W
Power Dissipation @ T_C=25℃	P_D	20	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	71.4 (Note 2)	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	6.25	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

Note : 1. Single Pulse , Pw≦380μs,Duty≦2%.
2. When mounted on a PCB with the minimum pad size.

Characteristics (Ta=25°C)

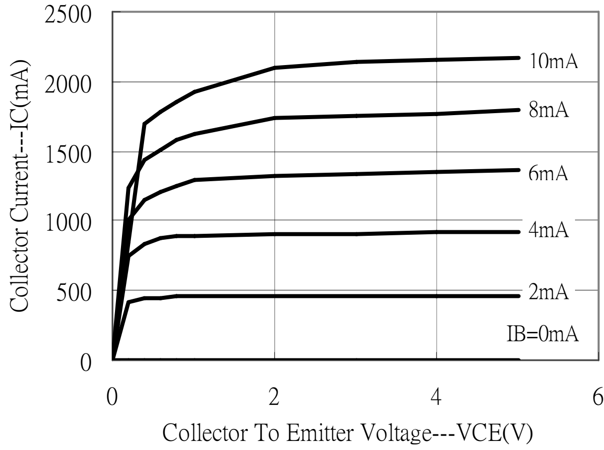
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{CEO(SUS)}$	80	-	-	V	I_C=30mA, I_B=0
I_{CES}	-	-	10	μA	V_{CE}=80V, V_{BE}=0
I_{EBO}	-	-	50	μA	V_{EB}=5V,I_C=0
*$V_{CE(sat)}$ 1	-	0.3	0.6	V	I_C=8A, I_B=0.4A
*$V_{CE(sat)}$ 2	-	-	1.5	V	I_C=5A, I_B=50mA
*$V_{BE(sat)}$	-	1.0	1.5	V	I_C=8A, I_B=0.8A
*h_{FE}	60	-	-	-	V_{CE}=1V, I_C=2A
*h_{FE}	40	-	-	-	V_{CE}=1V, I_C=4A
f_T	-	50	-	MHz	V_{CE}=6V, I_C=500mA, f=20MHz
Cob	-	130	-	pF	V_{CB}=10V, f=1MHz

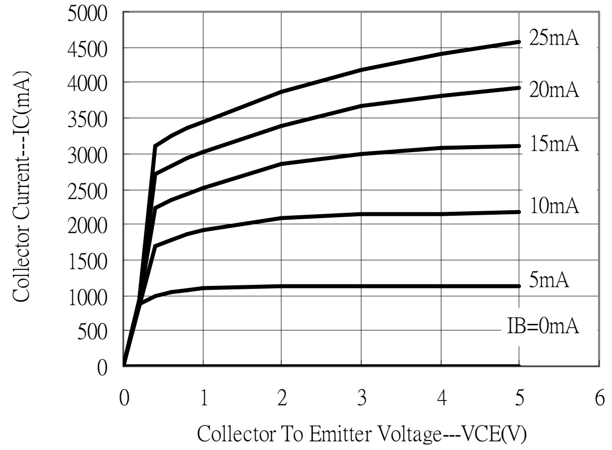
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

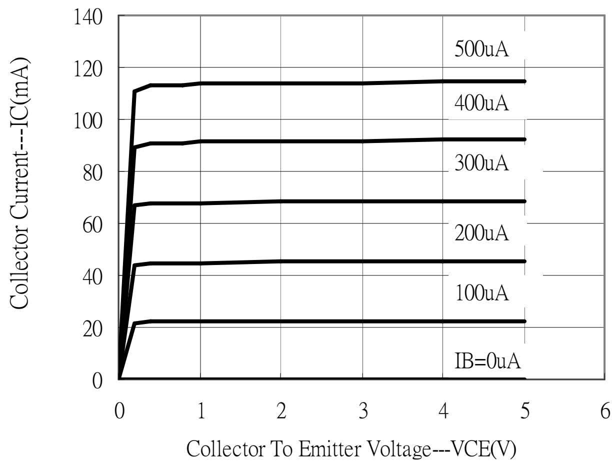
Classification of $V_{CE(sat)}$ 2

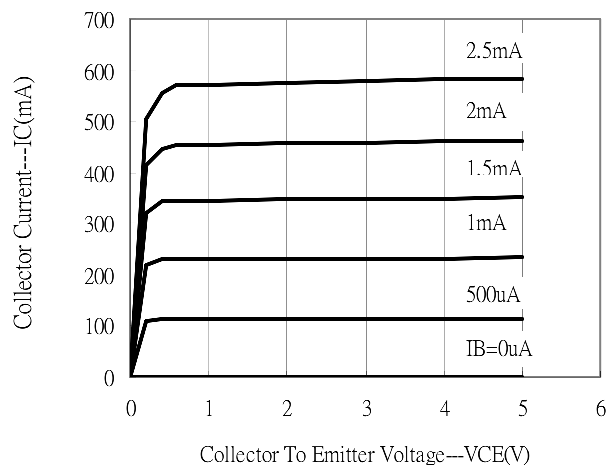
Rank	KB	KC	N
Range	<0.62V	0.58V~0.82V	0.78V~1.5V

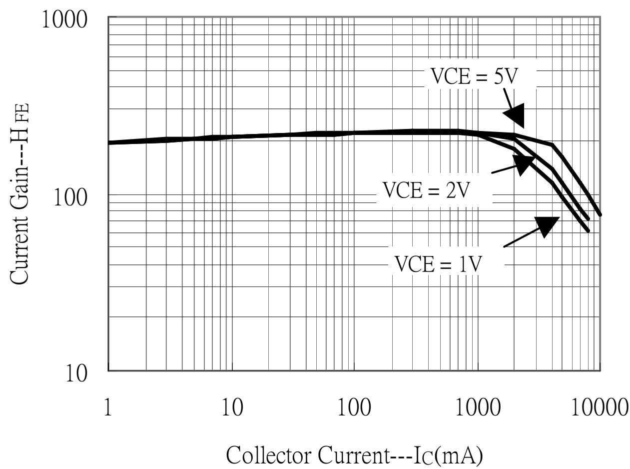
Typical Characteristics

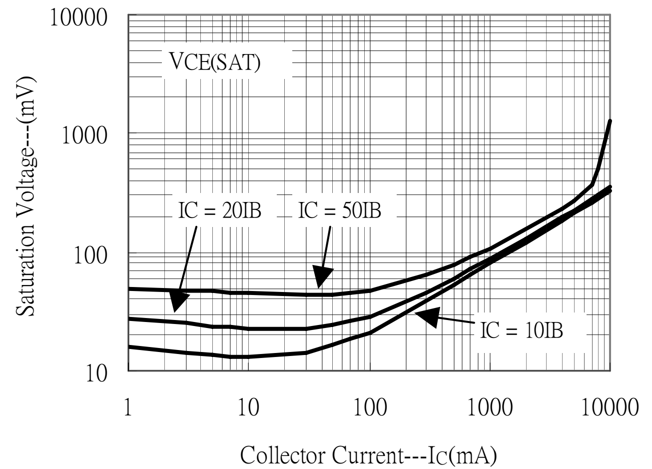




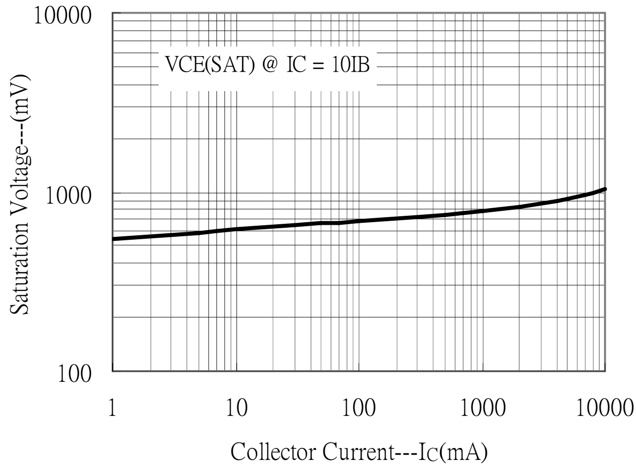


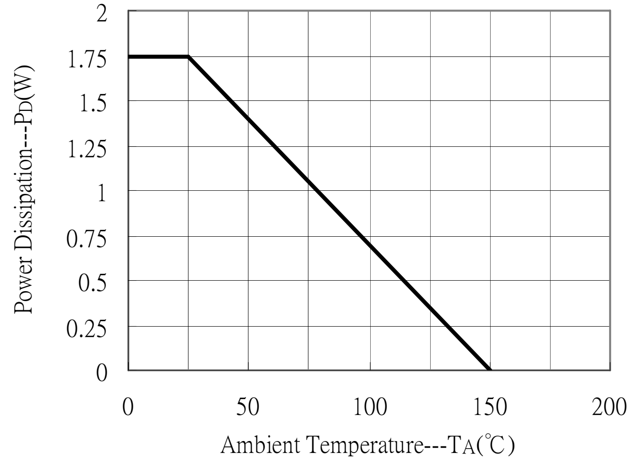


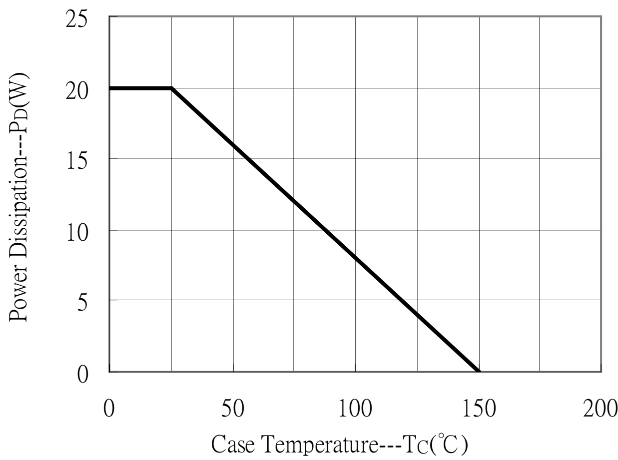




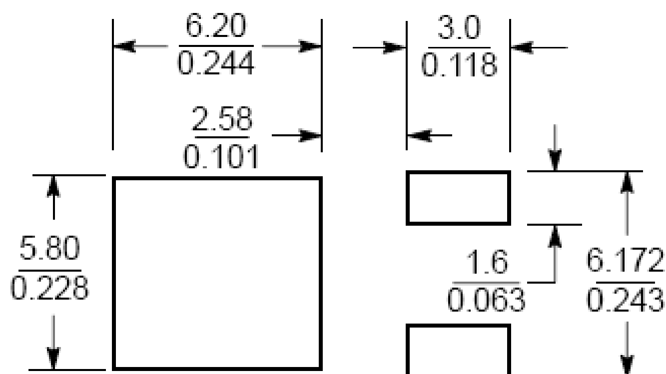
Typical Characteristics(Cont.)



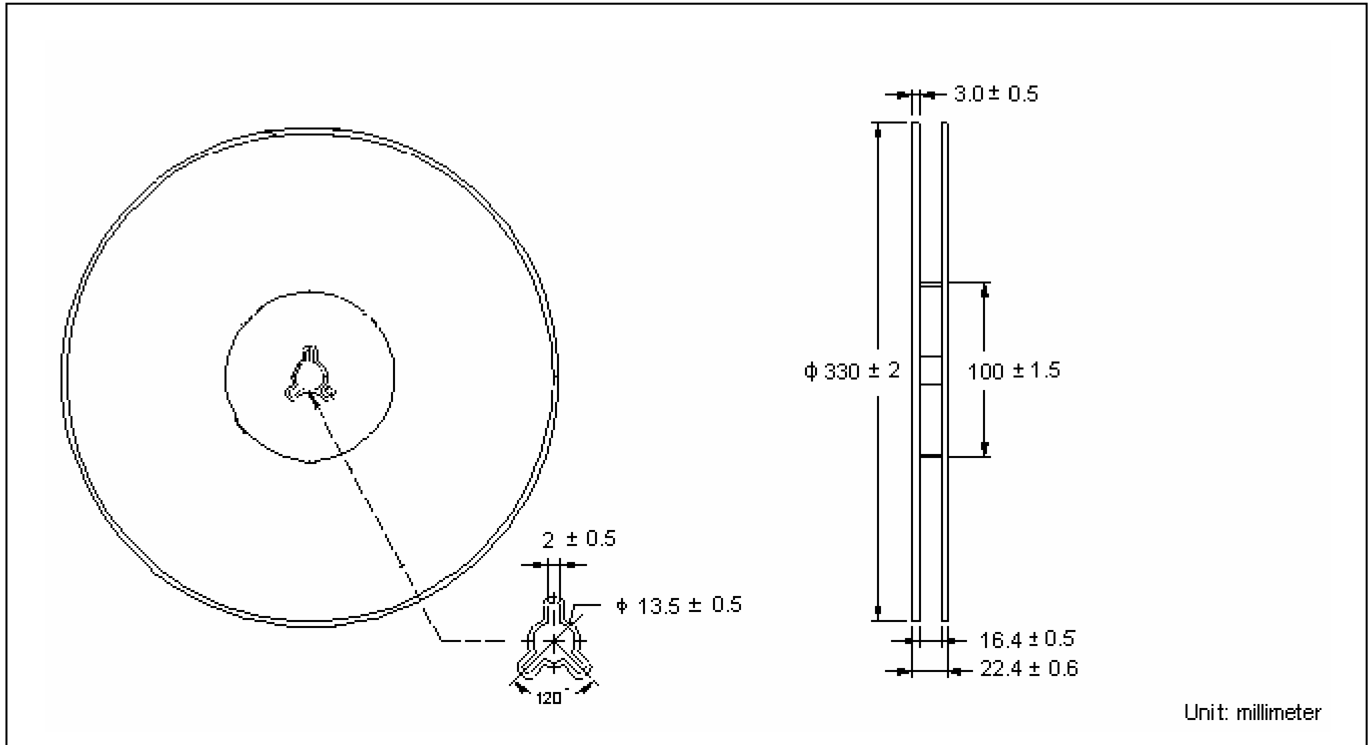




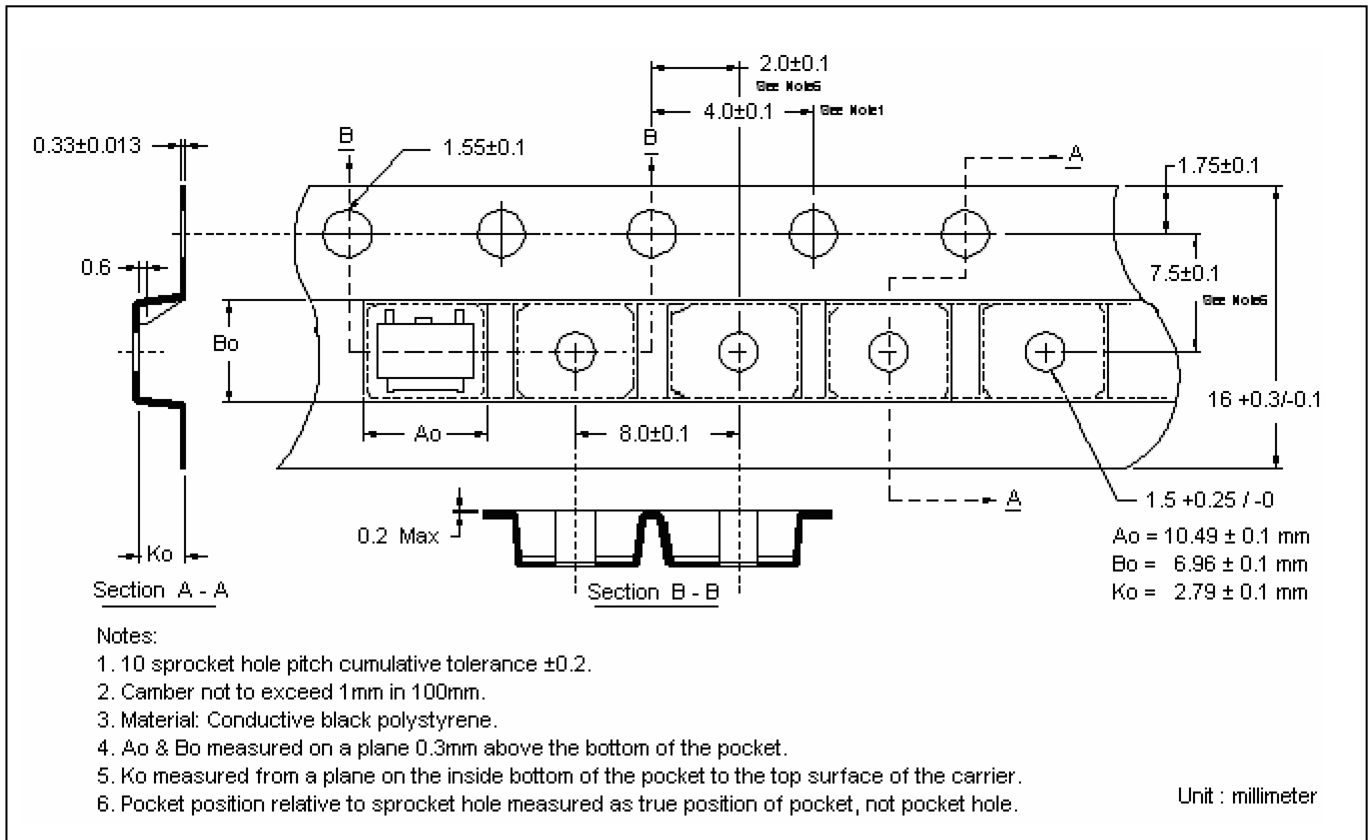
Recommended soldering footprint



Reel Dimension



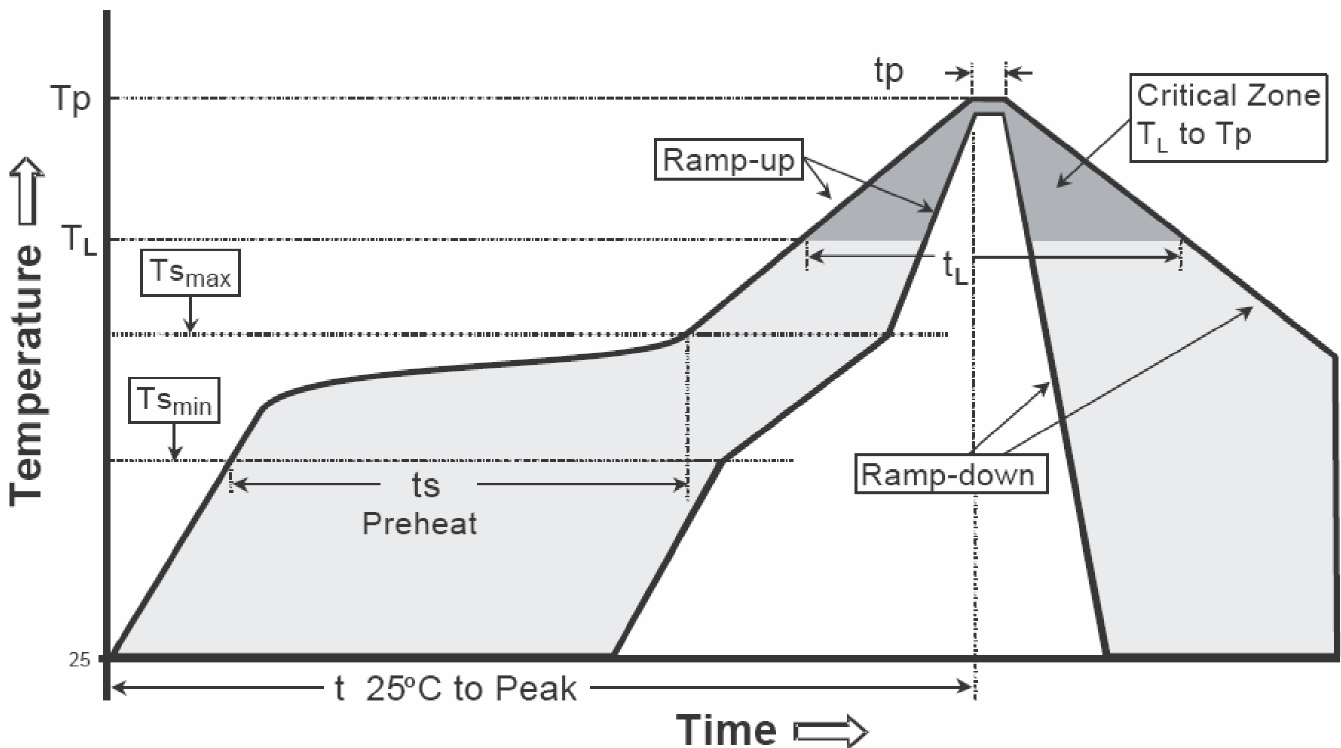
Carrier Tape Dimension



Recommended wave soldering condition

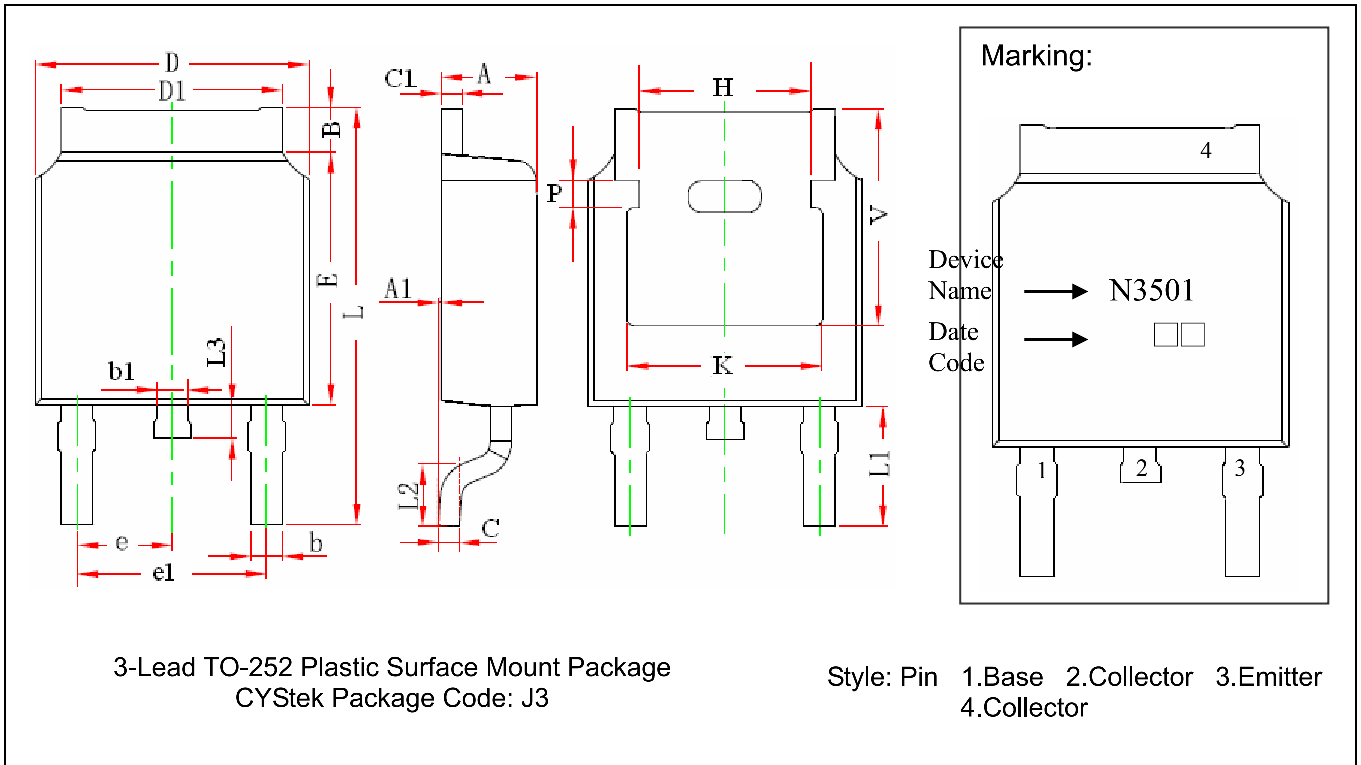
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package
CYStek Package Code: J3

Style: Pin 1.Base 2.Collector 3.Emitter 4.Collector

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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